C onduction an isotropy, H all e ect and m agnetoresistance of (T M T SF) $_2$ R eO $_4$ at high tem peratures

Bojana Korin-Ham zic Institute of Physics, P.O. Box 304, HR-10001 Zagreb, Croatia

Em il Tafra, Mario Basletic, and Am ir Ham zic Department of Physics, Faculty of Science, P.O. Box 331, HR-10002 Zagneb, Croatia

Gabriele Untereiner and Martin Dressel

1. Physikalisches Institut, Universitat Stuttgart, Pfa enwaldring 57, D-70550 Stuttgart, Germany (D ated: M arch 22, 2022)

We investigated the transport properties of the quasi-one-dimensional organic metal $(TM T SF)_2 ReO_4$ above the anion-ordering metal-insulator transition $(T_{AO} 180 \text{ K})$. The pronounced conductivity anisotropy, a small and smoothly temperature-dependent H all e ect; and a small, positive, and temperature-dependent magnetoresistance are analyzed within the existing Ferm i-liquid and non-Ferm i-liquid models. We propose that the transport properties of quasi-one-dimensional Bechgaard salts at high temperatures can be described within the Ferm i-liquid description.

PACS num bers: 74.70 K n, 72.15.G d, 71.10 Pm

I. IN TRODUCTION

Highly anisotropic organic conductors (TM T SF)₂X $(X = PF_6, CD_4, \ldots)$, the so-called Bechgaard salts, exhibit a high conductivity at room temperature and a m etallic behavior down to the low tem peratures where, under applied pressure and/orm agnetic eld, their electronic ground states may exhibit a variety of collective e ects such as superconductivity, spin-density wave, eld induced spin-density wave state with a com plex subphase structure, quantum Halle ect, etc. Many of these phenom ena are related to the low -dim ensional nature of the electronic spectrum . The quasi-one-dimensionality (1D) is a consequence of the crystal structure, in which the TM TSF molecules are stacked in columns (a direction), along which the highest conductivity occurs. These parallel columns form sheets that couple in the intermediate conductivity (b direction) and form conducting planes. Perpendicular to these planes (along the c direction), the coupling is the weakest and consequently this is the least conductivity direction. It is usually taken that the ratios of the resulting conductivity anisotropy and the bandwidth are $a: b: c = (t_a)^2 : (t_b)^2 : (t_c)^2 = 10^5 : 10^3 :$ 1.

There is a long standing controversy on whether the transport properties of the quasi-1D systems (such as Bechgaard salts) should be understood in terms of the usual Ferm i-liquid (FL) theory or the Luttinger-liquid (LL) theory.^{2,3,4} The nature of the m etallic phase of interacting electron systems depends strongly on the dimensionality. It is theoretically well established that the conventional FL theory of 3D m etals cannot be applied to the interacting electrons which motion is conned to one dimension. Instead, they form a LL state, with physical properties dimension that of a FL, and in which

the spin and the charge of an injected electron can move independently. In other words, the quasi-particle excitations, that are present in a FL, are replaced by separate collective spin and charge excitations, each propagating with a di erent velocity. LL system s exhibit non-FL-like tem perature and energy power-law behavior, and with exponents that are interaction dependent. It is expected that strongly anisotropic Bechgaard salts, with open Ferm i surfaces, may exhibit non-FL like properties at high tem peratures (where the therm all energy exceeds the transverse coupling) that lead to the loss of coherence for the interchain transport. The crossover from LL behavior to the coherent one is expected as the tem perature (or frequency) is decreased.^{5,6}

W hile many of the low temperature properties of the Bechgaard salts are well described by the FL theory,¹ their high temperature phase is still poorly understood. The optical conductivity data were interpreted as a strong evidence for non-FL behavior and the powerlaw asymptotic dependence of the high frequency optical mode has been associated to the LL exponents.^{7,8} On the other hand, the interpretation of the transport and m agnetic susceptibility results has not been unique, as some data were interpreted in the fram ework of the LL m odel,^{9,10} whereas for the others, the FL theory was used.^{11,12}

Recently, the long m issing basic experiment, the tem – perature dependence of the Hall coe cient in the metallic phase of the quasi-one-dimensional organic conductor $(TM TSF)_2 PF_6$ was performed by two groups.^{13,14} Their results were obtained for dimensional organic and were interpreted dimently, i.e. using the conventional FL theory¹³ and LL concept.¹⁴ M ore recently, the theoretical calculations of the in-chain and inter-chain conductivity as well as of the Halle ect in a system of weakly coupled LL chains have been performed, ^{15,16} giving the explicit expressions as a function of tem perature and frequency, but the m easurem ents of dc transport in (TM TSF)_2PF_6 along the c -axis are not fully understood theoretically from a LL picture. 9,15

The aim of this paper is to contribute to these, still open, questions about the nature of the m etallic state in Bechgaard salts by studying the anisotropic transport properties of yet another m em ber of the Bechgaard salts fam ily $(TM T SF)_2 R \in O_4$.

The choice of a salt with $X = ReO_4$ is based on the uni ed phase diagram, where the anisotropy of the system is varied by changing the anion.¹⁷ In this sense $(TMTSF)_2 ReO_4$ is more anisotropic than (TMTSF)₂PF₆: the empirical correlations of various structural parameters for a series of (TMTSF)2X salts were explored¹⁸ by using a van der W aals-like estim ate for the radius of the counterion X . The obtained values for the anion radius (at 300 K) clearly show that them axin alvalue is for the ReO₄ anion: R_i (C D₄) = 2:64 A < $R_{i}(PF_{6}) = 2:81 A < R_{i}(ReO_{4}) = 2:94 A$. Furtherm ore, the band structure of $(T M T SF)_2 X$ was calculated by the tight-binding scheme $_{r}^{19}$ and the values for the ratio of the transfer integrals $t_a = t_b$ at 300 K were 14, 17 and 18 (for $X = PF_6$, C 10₄ and R eO₄ respectively). Therefore, the highest value for $X = ReO_4$ indicates that this salt is m ore an isotropic than $X = PF_6$.

(TMTSF)₂ReO₄ exhibits a metal-insulator anion-180 K²⁰. This transiordering transition at T_{AO} tion coincides with the periodic ordering of the noncentrosymmetric ReO₄ anions. It is accompanied by a large distortion of the molecular stacks, which doubles the unit cell in all three directions, and consequently gives rise to a sharp increase of the electrical resistivity. We present the high tem perature (above T_{AO}) conductivity results at am bient pressure (for all three current directions), Halle ect in a standard geom etry (current parallel to the highest conductivity direction) and magnetoresistance (MR) (in the least conductivity direction). The pronounced conductivity anisotropy, a small and sm oothly tem perature dependent Halle ect and a small, positive and temperature dependent MR will be analyzed within the Ferm i-liquid and non-Ferm i liquid models. A though not fully conclusive, our data favor the FL description.

II. EXPERIMENT

The m easurem ents were done in the high tem perature region (150 K < T < 300 K) and in magnetic elds up to 9 T.D uring the eld sweeps the tem perature was stabilized with a capacitance therm on eter. All the single crystals used come from the same batch. Their a direction is the highest conductivity direction, the b^0 direction (with interm ediate conductivity) is perpendicular to a in the a {b plane and the c direction (with the low est conductivity) is perpendicular to the a {b (and a {b⁰) plane. The resistivity data, presented here, are for a, b^0 and

c axes. For the b^0 and c measurements, the samples were cut from a long crystal and the contacts were placed on the opposite a {c (b^0) and a {b⁰ (c) surfaces (30 m diameter gold wires stuck with silver paint). The samples were cooled slow ly (3 K /h) in order to avoid irreversible resistance jumps (caused by microcracks), well known to appear in all organic conductors.

The Halle ect was measured in a standard geometry (jka, B kc?). Two pairs of H all contacts and one pair of current contacts were made on the sides of the crystalby evaporating gold pads to which the gold wires were attached with silver paint. An ac current (10 A to 1 mA, 22 Hz) was used. For T < T_{AO} a dc technique was used because of the large resistance increm ent. Particular care was taken to ensure the tem perature stabilization. The Hall voltage was measured at xed tem peratures and in eld sweeps from B_{max} to $+B_{max}$ in order to eliminate the possible mixing of the magnetoresistance com ponent. At each tem perature the Hall voltage was measured for both pairs of Hall contacts to test and/or control the hom ogenous current distribution through the sample. The Hall voltage V_{xy} was determined as $[V_{xy}(B) = V_{xy}(B)]=2$ and the Hall coe cient R_{H} was obtained as $R_{H} = (V_{xy}=IB)t$ (I is the current through the crystal and t is the sam ple thickness). The Hall signal was linear with magnetic eld up to 9 T in the whole tem perature region investigated.

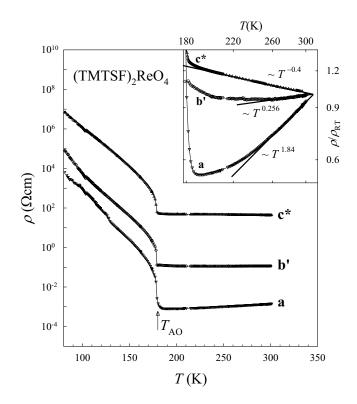
The MR, de ned as $=_0 = [(B) (0)] = (0)$, was measured in the jkc^2 , $B kb^0$ geom etry. Single crystalsam – ples were cut to the required length along the a axis with a razor blade and four electrical contacts were m ade with silver paint. The dimensions along a, b^0 and c for the two sam ples were 1.197 0.558 0.056 mm³ and 1.334 0.553 0.056 mm³ respectively. An actechnique with 10 A and 22 Hz was used.

III. RESULTS

Figure 1 shows the high temperature (77 K < T < 300 K) dependence of the resistivity, measured along the three di erent crystal directions. The room temperature resistivity values for $_{\rm a}$ (jka), $_{\rm b^{\circ}}$ (jkb⁰) and $_{\rm c}$ (jkc[?]) are 1.45 10³ cm, 0.117 cm, and 44 cm respectively. A sharp rise of the resistivity below 180 K is a direct manifestation of the anion-ordering (metal-insulator) transition at $T_{\rm AO}$ (the value $T_{\rm AO}$ = 178.8 K, obtained from the derivatives of our data, is in good agreem ent with the literature¹).

Let us now discuss separately the resistivity results for each direction, as they show pronounced di erences. These are even more evident from the inset of Fig. 1, where the temperature dependence of resistivity data norm alized to their room temperature values ($_{\rm RT}$) are given.

The a-axis resistivity agrees well with the previously published data.²⁰ Below T_{AO} the resistivity increases exponentially with an activation energy that can be es-



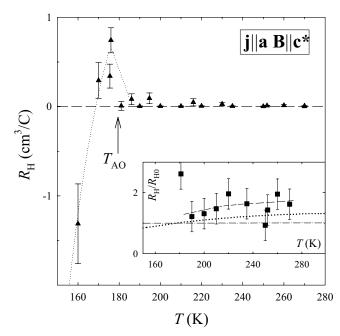


FIG.1: The temperature dependence of the resistivities $_{a}$, $_{b^{0}}$, $_{c}$ (measured along the three crystal directions). Inset: log-log plot of $_{a}$, $_{b^{0}}$, $_{c}$ (norm alized to their respective room temperature values) vs. temperature.

tim ated using the phenom enological law for a simple sem iconductor [exp(=k_BT)]. The obtained value = (1000 100) K is the same for all three current directions. Above T_{AO} the a-axis resistivity has a metallic-like behavior, and the decrease of the resistivity between the room temperature down to T 240 K can be tted to a a T^{1:84} power-law. A weaker decrease of the resistivity below T 240 K could be ascribed, in our opinion, to the precursor e ects due to the anion ordering.

The interm ediate conductivity direction also shows a m etallic-like behavior; it is however rather weak, and for only T > 257 K (i.e. above the minima) it follows a $_{\rm b^0}$ T^{0:25} dependence. At lower temperatures $_{\rm b^0}$ starts increasing. We point out that, to the best of our know ledge, this is the st time that such a behavior of $_{\rm b^0}$ has been found in a member of the Bechgaard salts fam ily. The resistivity for the b⁰ axis has been rather poorly investigated up to now . Nevertheless, it is know n that for (TM TSF)₂PF₆ a monotonic, metallic-like decrease with decreasing temperature follows a $_{\rm b^0}$ T dependence.^{21,22}

Finally, for the lowest conductivity, c direction, the resistivity increases with the decreasing temperature, and in the region 190 K < T < 300 K it follows the $_{\rm c}$ T $^{0:4}$ law. A similar behavior of $_{\rm c}$ was found for (TM TSF)₂PF₆ in the same temperature region, although there is also a well characterized maximum at about 80 K

FIG.2: The temperature dependence of the H all coe cient $R_{\rm H}$. Inset: the normalized H all coe cient [with $R_{\rm H,0}$ given by the Eq. (4)]vs. temperature. D ashed line: a guide for the eye; dotted line: $R_{\rm H}$ (T) behavior predicted in a model where the electron relaxation time varies over the Ferm i surface – see text.

and a m etallic-like behavior below $\cdot^{21,23,24}$ On the other hand, for (TM TSF)₂C IO_4 c shows a m etallic-like behavior from room temperature down to the superconducting transition at 1.2 K (in the relaxed state) $\cdot^{12,24}$

It should be nally noted that all our data, presented in Fig. 1, are measured at am bient pressure.^{4,25} As it is known form ost organic conductors, much of the tem perature dependence of their conductivity at high tem peratures arises from the therm all expansion. Consequently, the constant-pressure data usually show di erent tem – perature dependences than the constant-volume data, and we shall come back to this point when comparing our constant-pressure data with theory which in general m akes predictions assum ing a constant volum e.

Figure 2 shows the tem perature dependence of the H all coe cient R_H of (TM T SF)₂ReO₄ above and below T_{AO}. The H all coe cient is positive in the metallic state, it changes its sign at the transition temperature and increases rapidly with further decrease of the temperature. The inset of Fig. 2 shows in greater details the H alle ect results in the metallic region, normalized to the calculated R_{H 0} value (and this will be discussed more in the following section).

The tem perature dependence of the transverse M R for T > 180 K, in the least-conducting direction jkc^2 , B kb⁰ and with B = 9 T (obtained on two sam ples) is presented in Fig. 3. The M R is positive, tem perature dependent and very sm all (increasing from 0.02% at room tem perature to 0:1% around 190 K). This particular

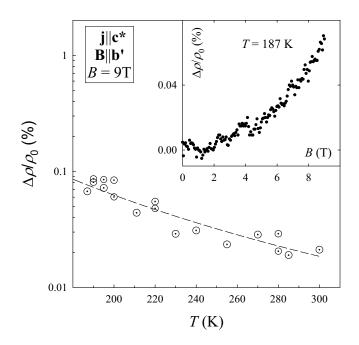


FIG.3: The temperature dependence of the transverse m agnetoresistance = $_0$ = $_c$ = $_c$ in the least-conductivity direction (jkc^2 , B kb⁰, B = 9 T). D ashed line indicates T³ dependence. Inset: = $_0$ = $_c$ = $_c$ vs. applied m agnetic eld at T = 187 K.

geom etry was chosen because, in the high tem perature region, the M R in the usual geom etry (jka, B kc[?]) was not detectable. The data below $T_{A\,0}$ are not given in F ig. 3. D ue to the strong increase of the resistivity with the decreasing tem perature, it was not possible to m easure accurately the M R in that region – nam ely, sm all tem perature variations resulted in resistance variations larger than those caused by the applied m agnetic eld, thus yielding to the signi cant scattering of the data.

In the m etallic state of $(TM TSF)_2 ReO_4$ at high tem – peratures the di erence R(T; B = 9 T) R(T; B = 0) is very small, and the only possible way to obtain reliable data was to measure MR at well-stabilized xed tem peratures and with zero- eld resistivity compensated before each eld sweep. Such a eld dependence is shown in the inset of Fig. 3 for T = 187 K: it is typical for all measured tem peratures, show ing a B^2 variation.

IV. D ISCUSSION

Before entering into a more detailed analysis of the transport measurem ents of $(T M T SF)_2 R eO_4$ in them etallic state (within the existing FL and non-FL models), we should emphasize that the direct comparison of the experimental results with the theoretical predictions is not straightforward. The theoretical calculations are usually done for the constant-volume temperature dependencies, whereas Bechgaard salts in the metallic regime show a large pressure coencile constant of the conductivity.²⁵ In

other words, to be able to directly com pare the constantvolum e (V) (T) theoretical data with the experimental constant-pressure (T) data (shown in Fig. 1), a conversion has to be performed. In our case we have used the same approach as it was done for $(TM TSF)_2AsF_6$ (Ref. 4) and $(TMTSF)_2 PF_6$,²⁶ because (to our know – edge) there are no experim entaldata for the therm alexpansion and compressibility of (TMTSF)₂ReO₄. However, as ReO₄ is a non-centrosymmetric anion, whereas PF_6 is a centrosymmetric one, such a conversion should be taken with some precaution due to the degree of arbitrariness that underlines the conversion procedure.²⁷ In the case of $(TM TSF)_2 PF_6$ the unit cell at 50 K and at am bient pressure was taken as a reference unit cell when the tem perature T is increased, a pressure P must be applied (at given T) in order to restore the reference volum e. Taking into account that in the metallic phase, a varies 25% perkilobar (for all T values), the m easured resistivity a is then converted into the constant-volum e value $a^{(V)}_{a}$ using the expression $a^{(V)}_{a} = a = (1 + 0.25P)^{26}$. The analogous procedure is applied for $\binom{(V)}{b^0}$, because it was found that both a and b increase under pressure at room temperature at a common rate of 25% kbar¹ (Refs. 4,28) and a = b is essentially T and P indepen- $25 \text{ K}^{4,28}$ W e have therefore converted dent above T our data using the same P values as for (TM TSF) $_2$ PF $_6$ and $(TMTSF)_2AsF_6$ that have been calculated from Refs. 4,26 and are presented in the inset of Fig. 4. For $_{c}^{(V)}$ the corrections were not made, because the data for (TM TSF)₂PF₆ in Ref. 9 were calculated di erently. N am ely, the variation of c with pressure is not the sam e for all tem peratures, and therefore we could not apply a sim ilar procedure without knowing the exact results for (TM TSF) $_2$ ReO $_4$.

The calculated values of constant-volum e resistivity for $a^{(V)}$ and $b^{(V)}_{b^0}$ are shown in Fig. 4. The deduced tem perature dependencies between 220 K and room tem pera- $T^{+\ 0:75}$ and b^{0} ture are a T^{0:64}. The comparison of these results with those for (TM TSF) $_2$ PF $_6$ (in the sam e tem perature range,^{9,14,22}) shows that a sim ilar behavior is found for $a^{(V)}$, whereas the b^{0} data were not calculated and $\binom{(V)}{c}$ T^{1:4}. Some important di erences between the various Bechgaard salts should be point out. At constant-pressure b° (T) for (TM TSF)₂PF₆ and $(TM TSF)_2 C D_4$ (R efs. 1,29) show s a m etallic-like behavior up to room temperature in contrast to our $b^{\circ}(T)$ data for $(TMTSF)_2 ReO_4$. On the other hand, while $_{\rm c}$ (T) for (TM TSF) $_2$ C 10 $_4$ shows also a metallic-like behavior, 23,24 in the case of (TM TSF)₂PF₆ _c (T) has a non-monotonic tem perature dependence going through a well characterized maximum at 80 K.We believe that these di erences in ${}_{b^{\circ};c}$ (T) behavior can be ascribed to a higher anisotropy in the (TM TSF) $_2$ ReO $_4$ compound.

The simplest model of electronic transport in metals is the D nude model,³⁰ where all relaxation processes are described by a single relaxation time \cdot . The anisotropy of the resistivity values can be accounted for by an

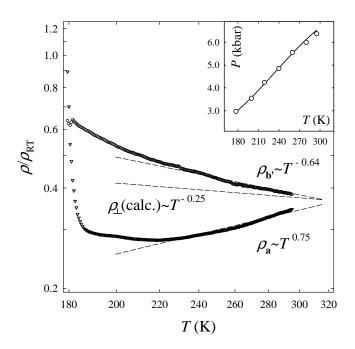


FIG. 4: The temperature dependence of the calculated constant-volume resistivities $_{\rm a}$ and $_{\rm b^0}$. Also shown is the calculated transverse resistivity $_2$ in the LL approach (see text for the details). Inset: Temperature dependence of the (e ective) pressure P values, deduced from Refs. 4,26 and used in our calculation.

anisotropic band m ass. G oing beyond the D rude m odel, the scattering rate may be frequency dependent. The simple approach of a hom ogeneous relaxation rate, how ever, can still not describe the di erent T dependences observed for a, b⁰ and c directions; hence it m ay provide evidence against the conventional FL picture. On the other hand, in (TM TSF)₂PF₆, the tem perature dependencies of $a^{(V)}$ (R ef. 31) and the Hallcoe cient, between room tem perature and down to the lowest tem peratures, were quite satisfactory compared with the FL theoreticalm odel where the electron relaxation time varies over the Ferm i surface.^{32,33} According to this model, in the high tem perature region (where $T > t_c$ 10 K and T < 300 K) the system is treated as a 2D FL. It is proth posed that a quasi-1D conductor behaves like an insulator $(d_a=dT < 0)$, when its e ective dimensionality equals 1, and like a metal (d $_a=dT > 0$), when its e ective dimensionality is greater than 1. For $(TM T SF)_2 R \in O_4$ and in the tem perature region T $> T_{AO}$, the tem perature dependence a $T^{+0.75}$, and d_a=dT > 0. This would then imply that (TM TSF)₂ReO₄ may also be interpreted in the fram ework of the same FL model like $(TMTSF)_2 PF_6$ (where $a^{(V)}$ $T^{+0:5}$).³¹ In other words, our nding suggests that (TM TSF)2ReO 4 is, like other Bechgaard salts, a 2D anisotropic metal at high tem peratures. It should be also pointed out here that the rate of the um klapp scattering along the chains was used for the calculation of $a^{(V)}$.³³ This relaxation time seem s inappropriate for the transport across the chains, but the exact calculations for ${}_{b^0}^{(V)}$ and ${}_{c}^{(V)}$ have not been performed yet. This is even more important because the tem perature dependences of ${}_{b^0}^{(V)}$ and ${}_{c}^{(V)}$ for other Bechgaard salts are dimensioned in the efform of the lack of a comprehensive transport theory (with anisotropic relaxation times) prevent us to go further in the comparison of ${}_{a}$, ${}_{b^0}$ and ${}_{c}$ data with the theoretical FL model.

The in-plane conductivity $_k$, inter-plane conductivity^{15,16} , and the Halle ect were calculated in a system of weakly coupled Luttinger chains. It was found that the inter-chain hopping (t₂ is a perpendicular hopping integral) is responsible for the m etallic character of the (TMTSF)₂X compounds, which would be otherwise M ott insulators. The tem perature (or the frequency !) power-law was determined, giving for the longitudinal and transverse resistivity, respectively,

$$_{\rm k}$$
 $(q_{=4})^2 T^{16K} {}^3$; (1)

$$_{2}$$
 T^{1 2}; (2)

where $g_{1=4}$ is the coupling constant for the um klapp process with 1/4~ lling, K is the LL exponent controlling the decay of all correlation functions (K = 1 corresponds to non-interacting electrons and K < 0.25 is the condition upon which the 1/4~ lled um klapp process becomes relevant) and = 1=4 (K + 1=K) 1=2 is the Fermi surface exponent.

The comparison of our experimental data, where $_{k} = _{a} T^{0:75}$, with the above LL theoretical model yields K = 0.234, the value that is in reasonable agreement with the value K = 0.23 for $(TM TSF)_2 PF_6$ obtained from the temperature dependence of $_{a}(T) T^{0:5}$ in the 100 K < T < 300 K range.^{14,16} For the frequency dependent conductivity parallel and perpendicular to the chains

$$_{\rm k}$$
 !^{16K 5} and ? !^{2 1} (3)

is predicted.¹⁵ Optical experiments on $(TM T SF)_2 X$ (X = PF_6 , AsF_6 , and CD_4) along the chains^{7,8} yield K = 0:23; the corresponding experiments perpendicular to the chains are in progress.³⁴ On the other hand, by us-= 0.234, we obtain for the transverse resistiving K ity ? $T^{0:25}$ (shown as dashed line in Fig. 4) while our experimental result gives bo T^{0:64}. Although it was mentioned previously that the calculated constantvolum e results have to be taken with som e precautions, 2.5 tim es higher exponent value obtained experithe m entally is nevertheless inconsistent with the predicted one. Here we have to point out that for $(TM T SF)_2 PF_6$ it was also concluded that the measurements of the dc transport along the transverse axis are not fully understood theoretically from the LL picture.³⁵ However, the theoretical model was compared with the c -axis resistivity results,^{9,15} which, in our opinion, is not the best

choice: the comparison should be applied to t_b and b^o in the rst place, rather than to t_c and c_c , because $t_b = t_c$.

The conclusion of this part of the work therefore is that the resistivity results for (TM T SF)₂ReO₄ can be wellexplained within the fram ework of both FL and LL m odels, but only for the a-axis. This is because there is no comprehensive theoretical FL transport approach (with anisotropic relaxation times) for $_{b^0}$ (T) and $_c$ (T), and on the other hand, the power-law for the temperature dependent transverse resistivity, proposed in the LL m odel, does not agree with our $_{b^0}$ (T) experimental results.

In the metallic state, the Hall coe cient R_{H} (Fig. 2) is sm all, positive (hole-like) and slightly tem perature dependent. In the vicinity of the T_{AO} phase transition, som e enhancem ent in the $R_{\rm H}$ (T) behavior can be observed (due to a pronounced scattering of the m easured values, the error bars are large in this region). The Hall coe cient changes its sign below T_{AO} and becomes negative (electron-like). For $T < T_{AO}$, \mathcal{R}_{H} (T) jalso shows a rapid increase with decreasing temperature, i.e. the Hall resistance is activated, as expected for a sem iconductor with the activation energy corresponding to that of the resistivity. In the inset of Fig. 2 the same results of the metallic region are shown in greater detail but normalized to the expected Hall coe cient constant value $R_{H,0} = 3:5$ 10³ cm³=A s. The dashed line in the inset is a guide to the eye. The R $_{\rm H\ 0}$ value is obtained using the tight-binding dispersion along the chains (the band is 1/4 led by holes and the scattering time is constant over the Ferm i surface) yielding^{36,37}

$$R_{H 0} = \frac{1}{ne} \frac{k_F a}{\tan(k_F a)}; \qquad (4)$$

where e and n are the electric charge and concentration of the carriers and $k_F \, a = = 4$. The carrier density of 1 hole/fu. gives n = 1:4 10^{21} cm 3 . As seen from the gure, the experimental results for R_H are, around 200 K, quite close to the expected $R_{\rm H}_{\rm 0}$ value, and show an increase of 30% at room temperature.

It has been show n^{16} that the Hall coe cient $R_{\rm H}$ of a system of weakly coupled LL chains, with the magnetic eld perpendicular to the chains and in the absence of the in-chain momentum relaxation, is independent of frequency or temperature. Moreover, $R_{\rm H}$ is given by a simple expression, corresponding to the non-interacting ferm ions, i.e. $R_{\rm H} = R_{\rm H \ 0}$. The temperature dependence of $R_{\rm H}$ could be addressed theoretically once the in-chain momentum relaxation processes are included,¹⁶ but the detailed calculations along these lines have not been done up to now. From this point of view, our $R_{\rm H}$ (T) results for T > 200 K, with a weak temperature dependence and with the values scattered about 20% around the $R_{\rm H \ 0}$ value, cannot exclude the possible LL interpretation.

However, the controversy with the LL theoretical model arises from the number of carriers participating in the dc transport. Namely, from the optical conductivity results for $(TM TSF)_2X$ salts^{7,8} (considered as the strong evidence for the LL behavior), it was concluded that all

the dc transport is due to a very narrow D rude peak containing only 1% of the spectral weight (arising from interchain hopping), whereas the remaining 99% is above an energy gap (of the order of 200 cm⁻¹), rem in iscent of a M ott insulating structure. Such a reduction of the carrier concentration n participating in the dc transport should give a factor of 100 higher $R_{\rm H}$ value, for both, calculated $R_{\rm H\ 0}$ and experimentally obtained values. It should be noted that this point was also established 13 for the H all e ect in (TM T SF)_PF_6. However, these m easurements were done in a di erent geometry (with respect to our data) and the temperature independent H all coe cient leads to the explanation in the fram ework of the FL theory with isotropic .

It has also been show n^{32} that R_H may be temperature dependent in a m odel where the electronic relaxation time varies over the Ferm i surface, i.e. the same model that satisfactorily describes a. The Hall coe cient then consists of two term s: $R_H = R_H^{(0)} + R_H^{(1)}$ where the st term is a tem perature-independent band structure contribution $R_{H 0}$, and the second term is the tem peraturedependent contribution determ ined by the variation of the relaxation time (k_y) over the (Ferm i surface) FS.³³ It was found that R_{H} is strongly tem perature dependent at low tem peratures, while at high tem peratures (T ţ,) it saturates at the $R_{H 0}$ value. The experimental results for R_{H} (T) and $_{a}$ (T) for (TM T SF)₂ PF₆ (that were previously explained by the LL concept¹⁴) were quantitatively compared with this model and a reasonably good agreement was found.³¹ In this model, however, the anion-ordering transition has not been taken into account, and we can compare it with our experim ental results only for T > 200 K. The dotted line in the inset of T^{0:7} Fig. 4 shows the theoretically predicted $R_{\rm H}$ (T) behavior (cf. Fig. 2a in Ref. 32) (obtained with the electron tunnelling am plitudes between the nearest and next-nearest chains t_b = 300 K and t_{b^0} = 30 K , respectively). As seen from Fig. 2, the temperature dependence of R_{H} (T), as well as the experimental values (albeit som ehow higher) satisfactorily follow the predicted Ferm i liquid description with an anisotropic relaxation time .

The tem perature dependence of the transverse M R for T > 180 K, and for the particularly chosen geometry (jkc², B kb⁰), presented in Fig. 3, exhibits a $_{\rm c} = _{\rm c}$ T ³ behavior. Our choice of geometry follows the prediction obtained in the simple FL model that is based on the band theory describing the transport at the open FS in the relaxation time approximation, i.e. for the isotropic $2^{23,24}$ A lihough we are aware that the isotropic

is a rather crude approximation for highly anisotropic systems such as Bechgaard salts, we will compare our results with this model, as there are no published calculations for an anisotropic . When the magnetic eld B is along the lowest conductivity direction c, the low - eld M R for the highest conductivity direction (a) is given by $_{a} = _{a} (!_{a})^{2} (!_{a}$ is the cyclotron frequency associated with the electron motion along the a axis, obtained

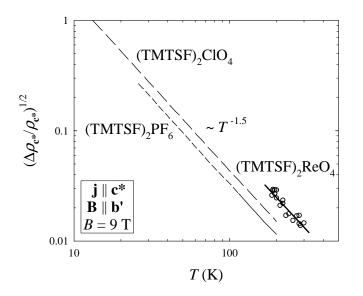


FIG.5: The tem perature dependence of the transverse m agnetoresistivity ($_{\rm c} = _{\rm c}$)¹⁼². Also shown are the data for (TM TSF)₂ClO₄ and (TM TSF)₂PF₆ (both from Ref.12 and norm alized to 9 T). The data for (TM TSF)₂PF₆ above 110 K are our unpublished results.

!c to=ta). The largest e ect is exin the model as !a pected for the current along the c axis and B along the intermediate conductivity b⁰ axis, because in this case $(!_{c})^{2}$ [where $!_{c} = (1=c_{0}\sim)eB cv_{a}$, c_{0} is _c = _c the velocity of light, ~ is the Planck constant, c is the lattice parameter and va is the Ferm i velocity along the chains]. It is evident that in this case ! !a. Indeed, in the high tem perature region, the MR in the usual geometry (jka, Bkc?) was not detectable (it was within the present resolution of our set-up), while for this particular geometry (jkc[?], B kb⁰), we obtained reliable results. Using the above simple relation (with the lattice parameter¹ c = 13:48 A), the experimentally measured _c = _c 0:02% at 300 K gives for the m ean free value path along the chains $l_a = v_a = 7.62 \text{ A}$. K now ing that the molecular spacing along the chains is a = 3.64 A, 2:1a, which implies a coherent it then follows that la in-chain carrier propagation (because $l_{a} > a$). On the other hand, the $_{h^{\circ}}(T)$ (below 257 K) and the $_{c}(T)$ results suggest di usive inter-chain carrier propagation. As already mentioned, with respect to $(TM T SF)_2 C D_4$ and $(TMTSF)_2 PF_6$, the $b^{\circ}(T)$ and c (T) variations in $(TM TSF)_2 ReO_4$ are also di erent. From this point of view, the surprising result emerges from the comparison of our present results for (TM TSF)2ReO4 with those for $(\text{IM} \text{TSF})_2 \text{CD}_4$ and $(\text{IM} \text{TSF})_2 \text{PF}_6$, obtained for the sam e geom etry.¹² This is shown in Fig. 5, where the data for all three systems are given as $(c_c = c_c)^{1=2}$ vs. tem -

7

perature.

The di erent $_{\rm c}$ (T) behavior in di erent salts obviously does not in uence the $_{c} = _{c}$ vs. T dependence. The sim ilarity between the presented data, i.e. the sam e tem perature dependence, is more than evident, and all three salts follow a ($_{\rm c} = _{\rm c}$)¹⁼² T^{1:5} variation (or, T^{1:5}). if using the above simple band picture, M oreover, for $(TMTSF)_2CD_4$ and $(TMTSF)_2PF_6$, the sam e tem perature dependence of the MR is also obtained at low tem peratures,¹² i.e. far below the tem perature (100 K) where the drastic changes in the physical properties are to be expected, due to the 1D ! 2D dim ensionality crossover from the LL to a coherent FL behavior, as the tem perature is low ered. 6,35 In line with these, the possible interpretation of our MR results is that the scattering mechanism, which governs the transport in the least-conducting direction, rem ains unchanged over the entire tem perature range that rules out any tem perature induced interlayer decoupling. The di usive, (i.e. the incoherent) inter-chain transport then assures a coupling between the chains, strong enough to allow the FL description for the transport properties at high tem peratures in Bechgaard salts. On the other hand, the possible appearance of the LL features in the transport properties should be expected in the more an isotropic $(TM TTF)_2X$ series, where the interactions play a crucial role.4,35

In conclusion, we perform ed the transport measurements in the metallic state of (TMTSF)2ReO4. The resistivity results for the a-axis may be well explained in the fram ework of both FL and LL m odels. On the other hand, the $b^{\circ}(T)$ and c(T) resistivity data do not agree with the prediction from the LL model, whereas the lack of a com prehensive FL transport theory (with an isotropic relaxation times) prevents us from reaching the nalconclusion concerning the FL approach. The Halle ect data suggest that the FL description with an isotropic remains valid throughout the metallic state. Finally, the m agnetoresistance m easurem ents do not give evidence of di erent regim es in the norm al state of the Bechgaard salts, which can be related to the 1D! 2D dimensionality crossover from the LL to a coherent FL behavior. Our nal proposal, therefore, is that the Ferm i-liquid model with anisotropic relaxation, i.e., the direction-dependent relaxation, should apply for the transport properties in

A cknow ledgm ent

Part of the work was supported by the Deutsche Forschungsgemeinschaft (DFG) under Grant No. Dr 228/10.

Bechgaard salts.

E lectronic address: bham zic@ ifs.hr

¹ T. Ishiguro, K. Yamaji, and G. Saito, Organic Supercon-

ductors, 2nd ed. (Springer, Berlin, 1998).

² H.J.Schulz, Int.J.M od.Phys.B 5, 57 (1991).

- ³ J.Voit, Phys.Rev.B 47, 6740 (1992).
- ⁴ D. Jerom e, in Organic Conductors, edited by J. Farges (Dekker, New York, 1994), p. 405.
- ⁵ C.Bourbonnais, F.C. reuzet, D.Jerom e, K.Bechgaard, and A.Moradpour, J.Phys. (France) Lett. 45, L755 (1984).
- ⁶ S. Bierm ann, A. Georges, A. Lichtenstein, and T. Giamarchi, Phys. Rev. Lett. 87, 276405 (2001).
- ⁷ M .D ressel, A .Schwartz, G .G runer, and L .D egiorgi, P hys. Rev. Lett. 77, 398 (1996).
- ⁸ A. Schwartz, M. Dressel, G. Gruner, V. Vescoli, L. Degiorgi, and T. Giam archi, Phys. Rev. B 58, 1261 (1998).
- ⁹ J. Moser, M. Gabay, P. Auban-Senzier, D. Jerome, K. Bechgaard, and J. M. Fabre, Euro. Phys. J. B 1, 39 (1998).
- ¹⁰ M. Dumm, A. Loidl, B. W. Fravel, K. P. Starkey, L. K. Montgomery, and M. D ressel, Phys. Rev. B 61, 511 (2000).
- ¹¹ M.Miljak, J.R.Cooper, and K.Bechgaard, Phys.Rev.B 37,4970 (1988).
- ¹² J.R.Cooper, L.Forro, B.Korin-Ham zic, K.Bechgaard, and A.Moradpour, Phys.Rev.B 33, 6810 (1986).
- ¹³ G. M ihały, I. Kezsmarki, F. Zamborszky, and L. Forro, Phys. Rev. Lett. 84, 2670 (2000).
- ¹⁴ J.M oser, J.R.Cooper, D.Jerom e, B.A lavi, S.E.Brown, and K.Bechgaard, Phys. Rev. Lett. 84, 2674 (2000).
- ¹⁵ A.Georges, T.Giam archi, and N.Sandler, Phys.Rev.B 61, 16 393 (2000).
- ¹⁶ A.Lopatin, A.Georges, and T.Giam archi, Phys.Rev.B 63,075109 (2001).
- ¹⁷ D. Jerom e, Science 252, 1509 (1991).
- ¹⁸ T. J. K istenm acher, M ol. Cryst. Liq. Cryst. 136, 361 (1986).
- ¹⁹ P.M.Grant, J.Phys. (Paris) Colloq. 44, C3-847 (1983).
- ²⁰ C.S.Jacobsen, H.J.Pedersen, K.M ortensen, G.R indorf, N.Thorup, J.B.Torrance, and K.Bechgaard, J.Phys.C: Solid State Phys. 15, 2657 (1982).
- ²¹ K.Bechgaard, C.S.Jacobsen, K.Mortensen, H.J.Pedersen, and N.Thorup, Solid State Commun.33, 1119 (1980).
- ²² J.M oser, PhD. thesis, University of Paris X I, 1999.

- ²³ J.R. Cooper, L.Forro, and B.Korin-Ham zic, Mol.Cryst. Liq.Cryst.119, 121 (1985).
- ²⁴ B.Korin-Ham zic, L.Forro, and J.R.Cooper, Mol.Cryst. Liq.Cryst.119,135 (1985).
- ²⁵ D. Jerom e and H. J. Schulz, A dv. Phys. 31, 299 (1982).
- ²⁶ P. Auban-Senzier, D. Jerome, and J. Moser, in Physical Phenomena at High Magnetic Fields III, edited by Z. Fisk, L.Gor'kov, and R.Schrie er (World Scientic, Singapore, 1999), p. 211.
- ²⁷ C. Burbonnais and D. Jerom e, in Advances in Synthetic M etals, Twenty Years of Progress in Science and Technology, edited by P.Bernier, S. Lefrant, and G. Bidan (Elsevier, New York, 1999), p. 206.
- ²⁸ H. J. Schulz, D. Jerom e, A. Mazaud, M. Ribault, and K. Bechgaard, J. Phys. (Paris) 42, 991 (1981).
- ²⁹ J.R.Copper and B.K orin-H am zic, in O rganic C onductors, (Ref. 4), p. 359.
- ³⁰ M. Dressel and G. Gruner, Electrodynamics of Solids (Cambridge University Press, Cambridge, 2002).
- ³¹ V.M.Yakovenko and A.T.Zheleznyak, Synth.M et. 120, 1083 (2001).
- ³² V.M.Yakovenko and A.T.Zheleznyak, Synth.M et.103, 2202 (1999).
- ³³ A.T.Zheleznyak and V.M.Yakovenko, Euro.Phys.J.B 11, 385 (1999).
- $^{\rm 34}\,$ K .Petukhov and M .D ressel (unpublished).
- ³⁵ S. Bierm ann, A. Georges, T. Giam archi, and A. Lichtenstein, in Strongly Correlated Ferm ions and Bosons in Low-D im ensional D isordered System s, Vol. 72, of NATO Science Series II, edited by I.V. Lerner, B. L. Althsuler, V. I.Fal'ko, and T. Giam archi (K luwer A cadem ic Publishers, D ordrecht, The N etherlands, 2002).
- ³⁶ J. R. Cooper, M. Miljak, G. Delpanque, D. Jerome, M. Wagner, J. M. Fabre, and L. Giral, J. Phys. (Paris) 38,1097 (1977).
- ³⁷ K.Makiand A.Virosztek, Phys. Rev. B 41, 557 (1990).